

BT139X-600E

Triac; sensitive gate

Rev. 03 — 23 September 2004

Product data sheet

1. Product profile

1.1 General description

Passivated, sensitive gate triac in a 'full pack' SOT186A (TO-220) plastic package.

1.2 Features

- High sensitivity in all four quadrants.

1.3 Applications

- General purpose bidirectional switching
- Phase control.

1.4 Quick reference data

- $V_{DRM} \leq 600$ V
- $I_{T(RMS)} \leq 16$ A
- $I_{TSM} \leq 155$ A
- $I_{GT} \leq 10$ mA (T2+ G+; T2+ G-; T2- G-)
- $I_{GT} \leq 25$ mA (T2- G+).

2. Pinning information

Table 1: Pinning

Pin	Description	Simplified outline	Symbol
1	main terminal 1 (T1)	<p>SOT186A (TO-220)</p>	<p>sym051</p>
2	main terminal 2 (T2)		
3	gate (G)		
mb	isolated		

3. Ordering information

Table 2: Ordering information

Type number	Package		Version
	Name	Description	
BT139X-600E	-	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3 lead TO-220 'full pack'	SOT186A

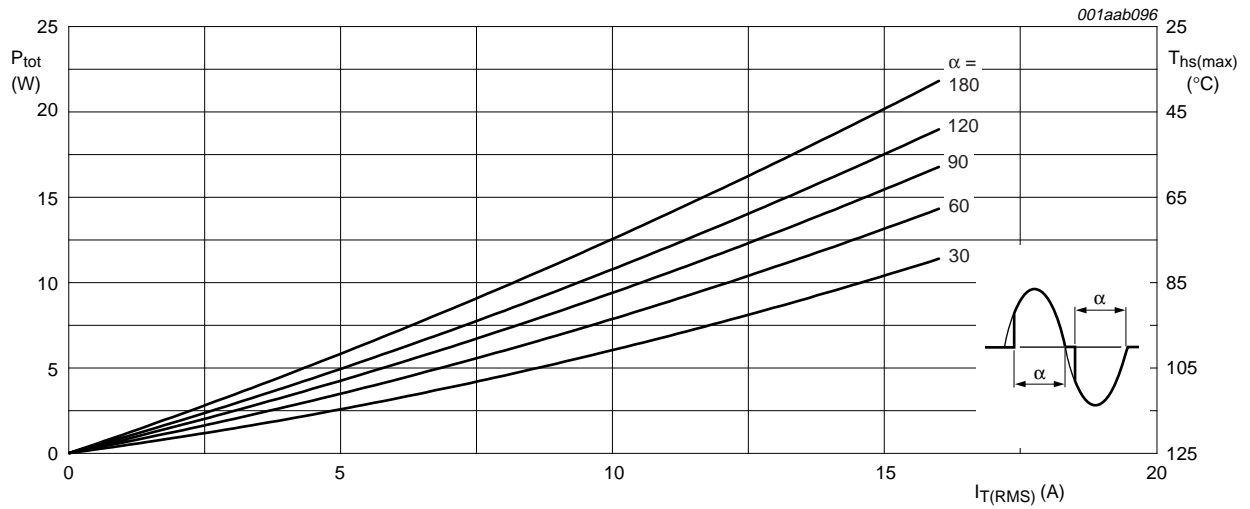
4. Limiting values

Table 3: Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

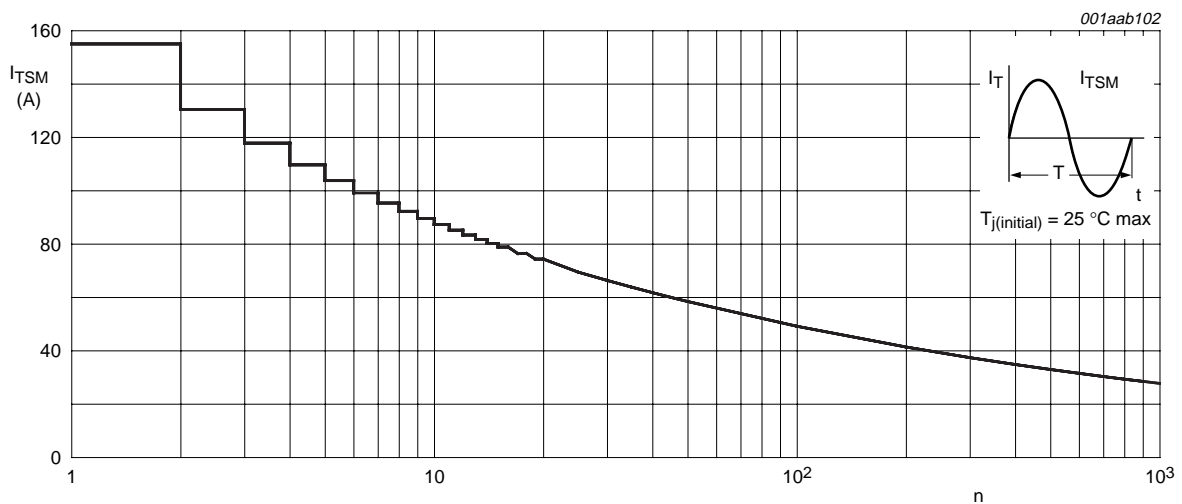
Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage		[1] -	600	V
$I_{\text{T(RMS)}}$	RMS on-state current	full sine wave; $T_{\text{hs}} \leq 38 \text{ }^\circ\text{C}$	-	16	A
I_{TSM}	non-repetitive peak on-state current	full sine wave; $T_{\text{j}} = 25 \text{ }^\circ\text{C}$ prior to surge			
		$t = 20 \text{ ms}$	-	155	A
		$t = 16.7 \text{ ms}$	-	170	A
I^2t	I^2t for fusing	$t = 10 \text{ ms}$	-	120	A^2s
di_{T}/dt	repetitive rate of rise of on-state current after triggering	$I_{\text{TM}} = 20 \text{ A}$; $I_{\text{G}} = 0.2 \text{ A}$; $di_{\text{G}}/dt = 0.2 \text{ A}/\mu\text{s}$			
		T2+ G+	-	50	$\text{A}/\mu\text{s}$
		T2+ G-	-	50	$\text{A}/\mu\text{s}$
		T2- G-	-	50	$\text{A}/\mu\text{s}$
		T2- G+	-	10	$\text{A}/\mu\text{s}$
I_{GM}	peak gate current		-	2	A
V_{GM}	peak gate voltage		-	5	V
P_{GM}	peak gate power		-	5	W
$P_{\text{G(AV)}}$	average gate power	over any 20 ms period	-	0.5	W
T_{stg}	storage temperature		-40	+150	$^\circ\text{C}$
T_{j}	junction temperature		-	125	$^\circ\text{C}$

[1] Although not recommended, off-state voltages up to 800 V may be applied without damage, but the triac may switch to the on-state. The rate of rise of current should not exceed 15 A/ μs .



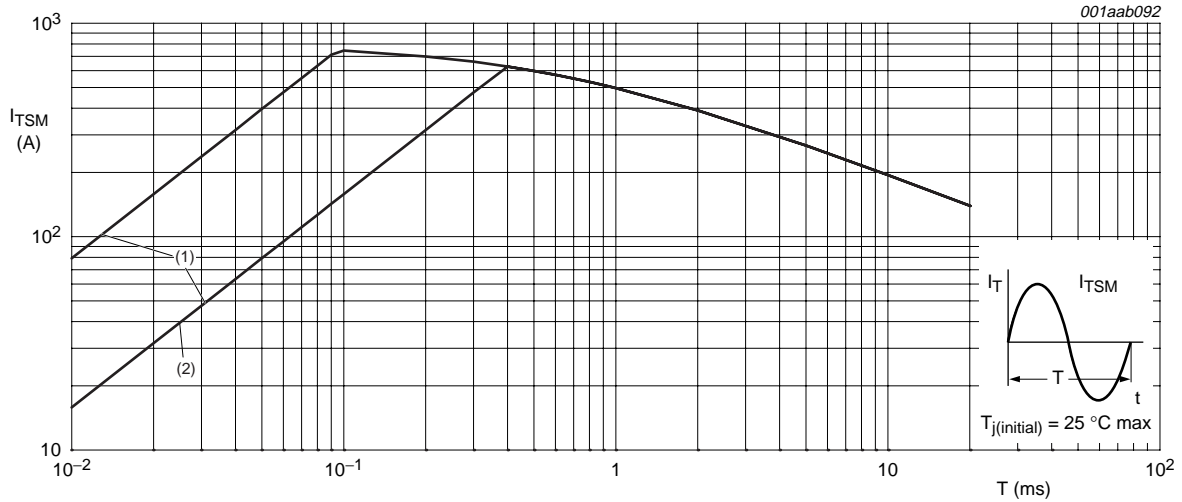
α = conduction angle.

Fig 1. Total power dissipation as a function of RMS on-state current; maximum values.



$f = 50$ Hz.

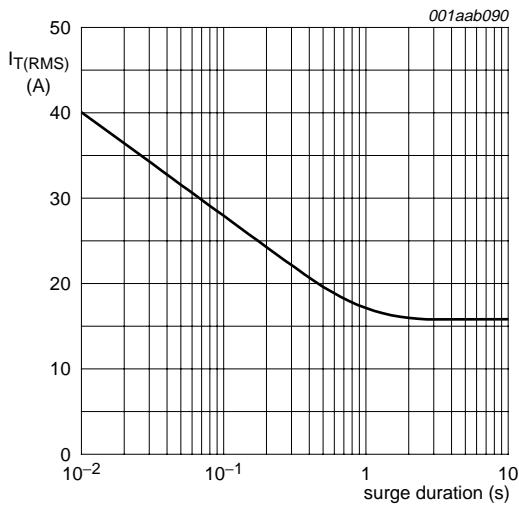
Fig 2. Non-repetitive peak on-state current as a function of the number (n) of sinusoidal current cycles; maximum values.



$t_p \leq 20$ ms.

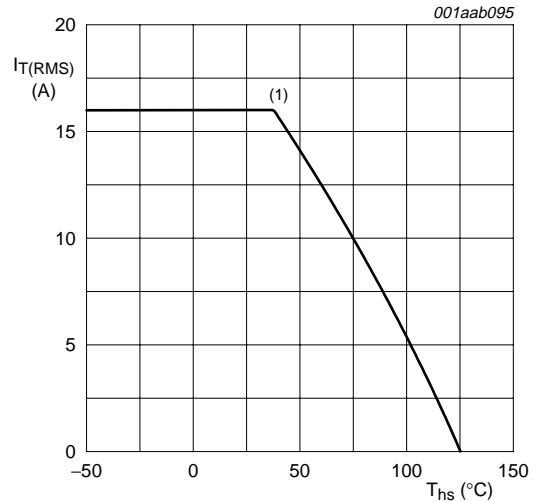
- (1) dI_T/dt limit.
- (2) T2- G+ quadrant.

Fig 3. Non-repetitive peak on-state current as a function of pulse width; maximum values.



$f = 50$ Hz; $T_{hs} \leq 38$ °C.

Fig 4. RMS on-state current as a function of surge duration; maximum values.



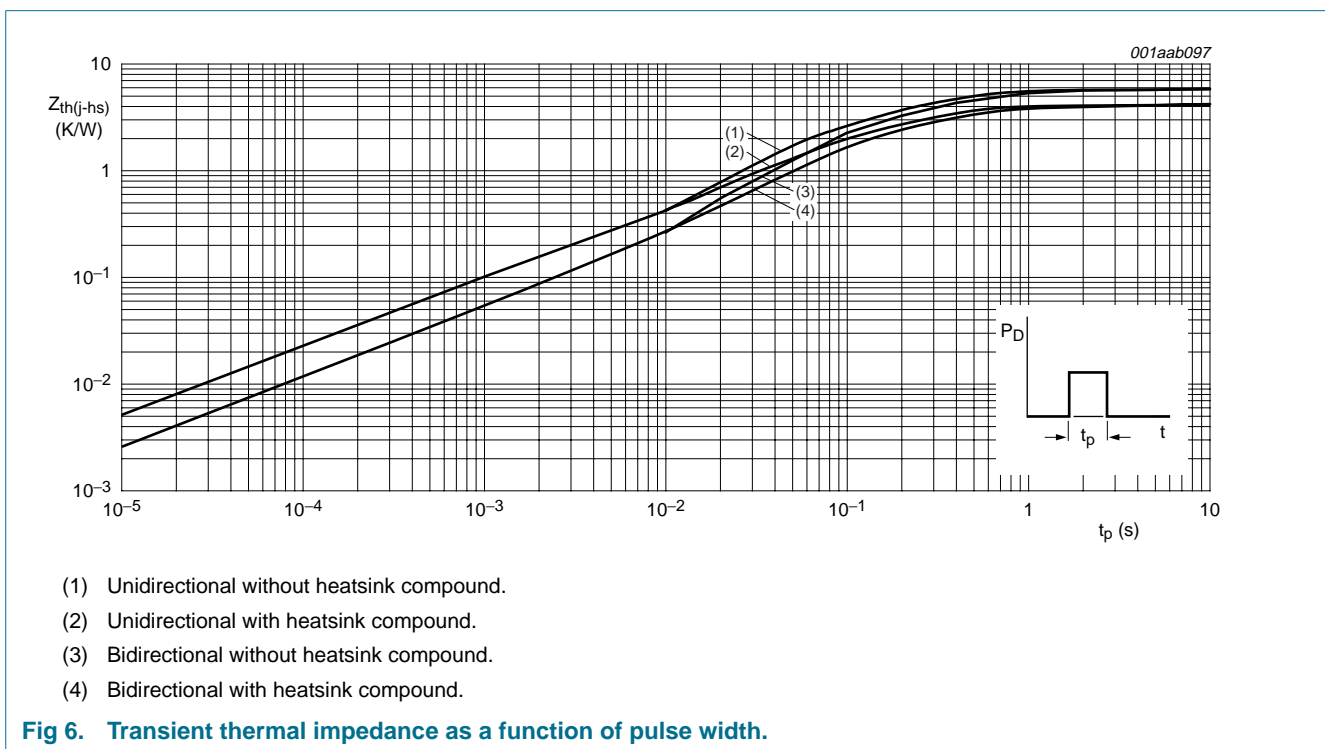
(1) $T_{hs} \leq 38$ °C.

Fig 5. RMS on-state current as a function of mounting base temperature; maximum values.

5. Thermal characteristics

Table 4: Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-hs)}$	thermal resistance junction to heatsink	full or half cycle with heatsink compound	-	-	4.0	K/W
		full or half cycle without heatsink compound	-	-	5.5	K/W
$R_{th(j-a)}$	thermal resistance junction to ambient	in free air	-	55	-	K/W



6. Isolation characteristics

Table 5: Isolation limiting values and characteristics

$T_{hs} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{isol}	RMS value isolation voltage from all three terminals to external heatsink	$f = 50$ to 60 Hz; sinusoidal waveform; R.H. $\leq 65\%$; clean and dust free	-	-	2500	V
C_{isol}	capacitance from pin 2 to external heatsink	$f = 1$ MHz	-	10	-	pF

7. Characteristics

Table 6: Characteristics

$T_j = 25\text{ °C}$ unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
I_{GT}	gate trigger current	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; Figure 8				
		T2+ G+	-	2.5	10	mA
		T2+ G-	-	4	10	mA
		T2- G-	-	5	10	mA
		T2- G+	-	11	25	mA
I_L	latching current	$V_D = 12\text{ V}$; $I_{GT} = 0.1\text{ A}$; Figure 10				
		T2+ G+	-	3.2	30	mA
		T2+ G-	-	16	40	mA
		T2- G-	-	4	30	mA
		T2- G+	-	5.5	40	mA
I_H	holding current	$V_D = 12\text{ V}$; $I_{GT} = 0.1\text{ A}$; Figure 11	-	4	45	mA
V_T	on-state voltage	$I_T = 20\text{ A}$; Figure 9	-	1.2	1.6	V
V_{GT}	gate trigger voltage	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; Figure 7	-	0.7	1.5	V
		$V_D = 400\text{ V}$; $I_T = 0.1\text{ A}$; $T_j = 125\text{ °C}$	0.25	0.4	-	V
I_D	off-state leakage current	$V_D = V_{DRM(max)}$; $T_j = 125\text{ °C}$	-	0.1	0.5	mA
Dynamic characteristics						
dV_D/dt	critical rate of rise of off-state voltage	$V_{DM} = 67\% V_{DRM(max)}$; $T_j = 125\text{ °C}$; exponential waveform; gate open circuit	-	50	-	V/ μ s
t_{gt}	gate controlled turn-on time	$I_{TM} = 20\text{ A}$; $V_D = V_{DRM(max)}$; $I_G = 0.1\text{ A}$; $dI_G/dt = 5\text{ A}/\mu$ s	-	2	-	μ s

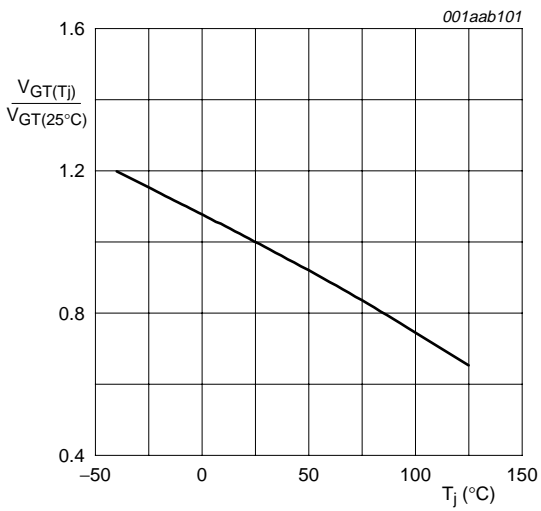
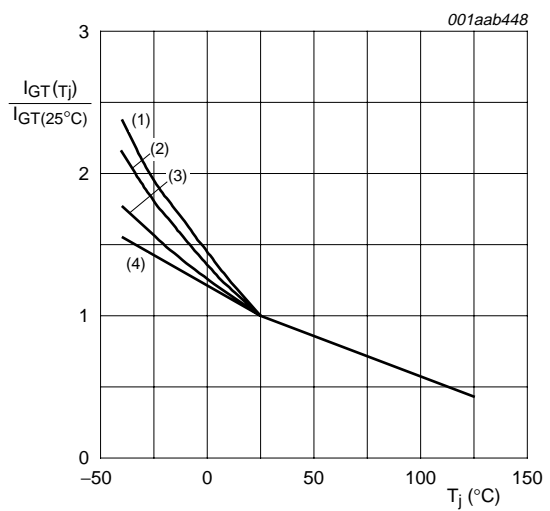
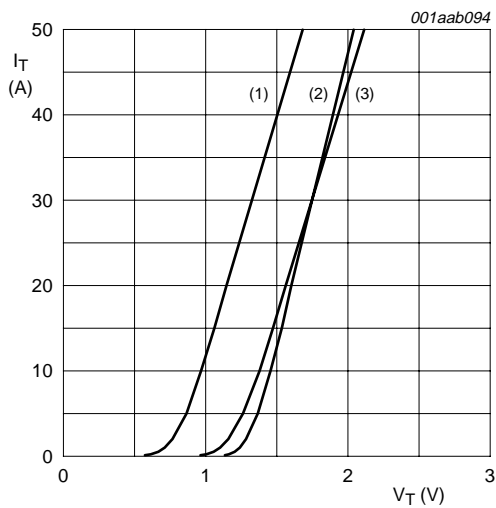


Fig 7. Normalized gate trigger voltage as a function of junction temperature.



- (1) T2- G+.
- (2) T2+ G-.
- (3) T2- G-.
- (4) T2+ G+.

Fig 8. Normalized gate trigger current as a function of junction temperature.



$V_O = 1.195 \text{ V.}$

$R_s = 0.018 \Omega.$

- (1) $T_j = 125 \text{ }^\circ\text{C; typical values.}$
- (2) $T_j = 25 \text{ }^\circ\text{C; maximum values.}$
- (3) $T_j = 125 \text{ }^\circ\text{C; maximum values.}$

Fig 9. On-state current characteristics.

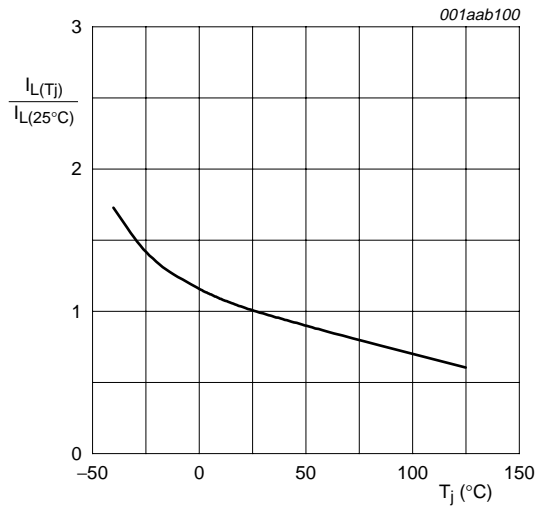


Fig 10. Normalized latching current as a function of junction temperature.

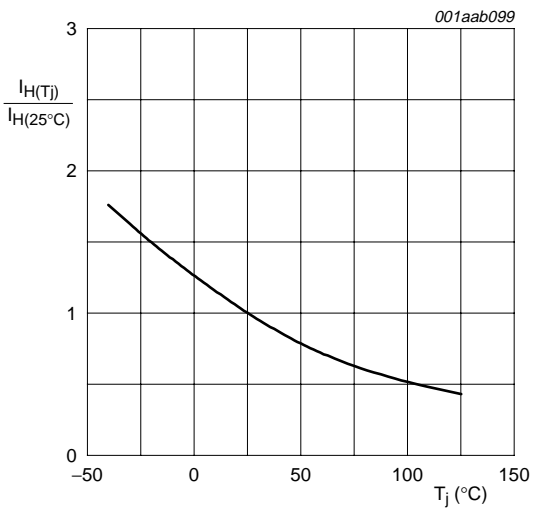


Fig 11. Normalized holding current as a function of junction temperature.

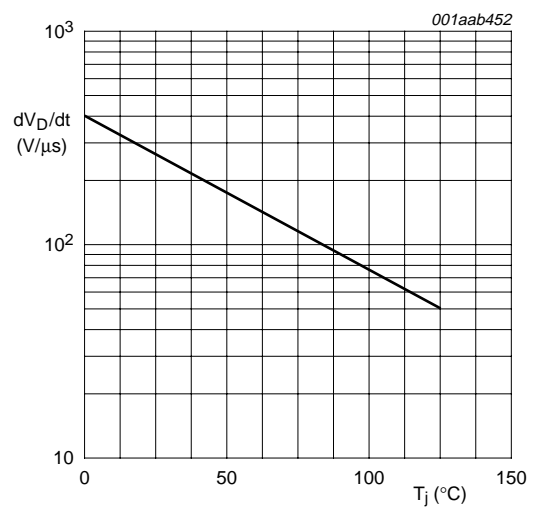


Fig 12. Critical rate of rise of off-state voltage as a function of junction temperature; minimum values.

8. Package information

Epoxy meets requirements of UL94 V-0 at 1/8 inch.

9. Package outline

Plastic single-ended package; isolated heatsink mounted;
1 mounting hole; 3 lead TO-220 'full pack'

SOT186A

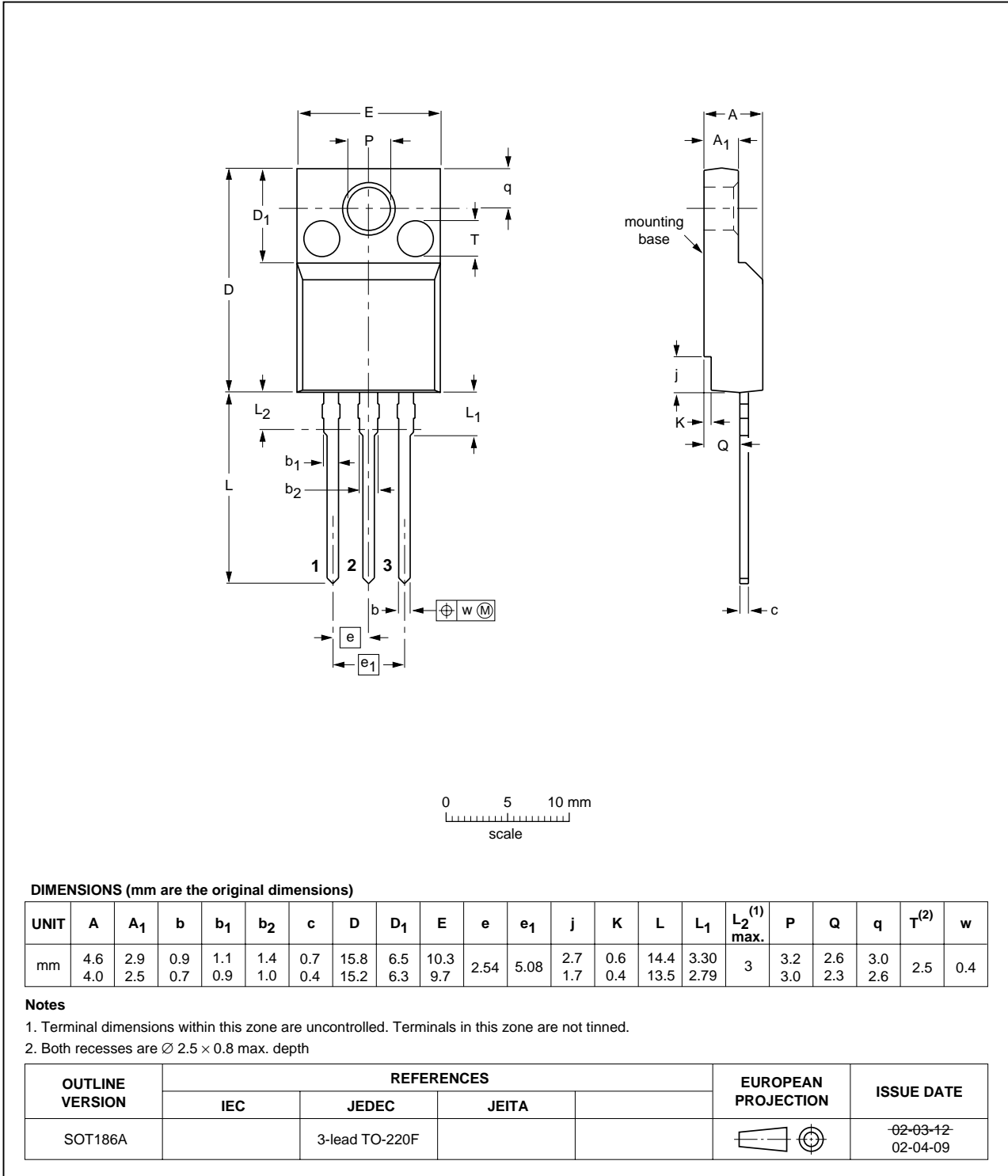


Fig 13. Package outline; SOT186A (TO-220).

10. Revision history

Table 7: Revision history

Document ID	Release date	Data sheet status	Change notice	Doc. number	Supersedes
BT139X_600E_3	20040923	Product data sheet	-	9397 750 13439	BT139X_600E_2
Modifications:	<ul style="list-style-type: none">The format of this data sheet has been redesigned to comply with the new presentation and information standard of Philips Semiconductors.				
BT139X_600E_2	20011001	Product specification	-	-	BT139X_SERIES_E_1
BT139X_SERIES_E_1	19970901	Product specification	-	-	-

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Level	Data sheet status ^[1]	Product status ^[2] ^[3]	Definition
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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[3] For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

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Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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Date of release: 23 September 2004
Document number: 9397 750 13439

Published in The Netherlands